

FRAM

MB85R256G

MB85R256G is a 256K-bits FRAM LSI using the ferroelectric process and CMOS process technologies for forming the nonvolatile memory cells.
Because FRAM is able to write high-speed even though a nonvolatile memory, it is suitable for the log management and the storage of the resume data, etc.
MB85R256G uses a pseudo-SRAM interface compatible with conventional asynchronous SRAM.

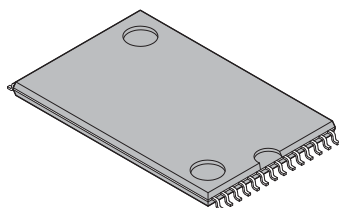
FEATURES

- Bit configuration : 32,768 words × 8 bits
- Read/write endurance : 10¹⁰ times/bit
- Peripheral circuit CMOS construction
- Operating power supply voltage : 2.7 to 3.6V
- Operating temperature range : -40°C to +85°C
- Data retention : 10 years (+70°C)
- Package : 28-pins, SOP flat package
: 28-pins, TSOP(1) flat package

ORDERING INFORMATION

Product name	Package	Remarks
TBD	Plastic • SOP, 28-pins (FPT-28P-M17) 8.60mm×17.75mm, 1.27mm pitch	-
TBD	Plastic • TSOP, 28-pins (FPT-28P-M19) 11.80mm×8.00mm, 0.55mm pitch	-
TBD	Plastic • SOP, 28-pins (FPT-28P-M17) 8.60mm×17.75mm, 1.27mm pitch	Embossed Carrier tape

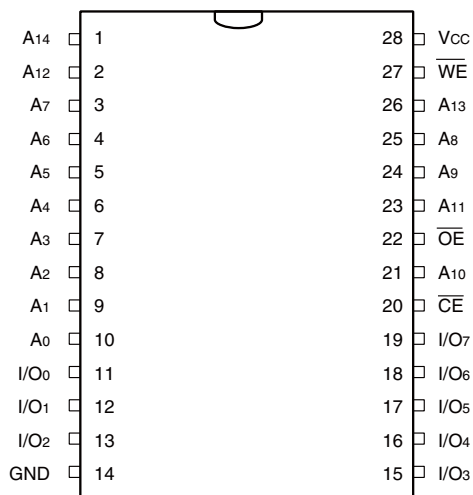
PACKAGE EXAMPLE OF REFERENCE



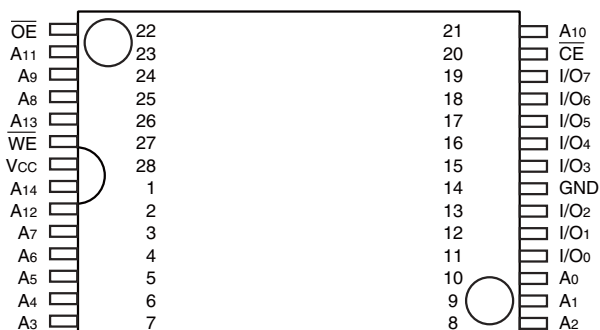
Plastic • TSOP, 28-pins
(FPT-28P-M19)

PIN ASSIGNMENT

(TOP VIEW)



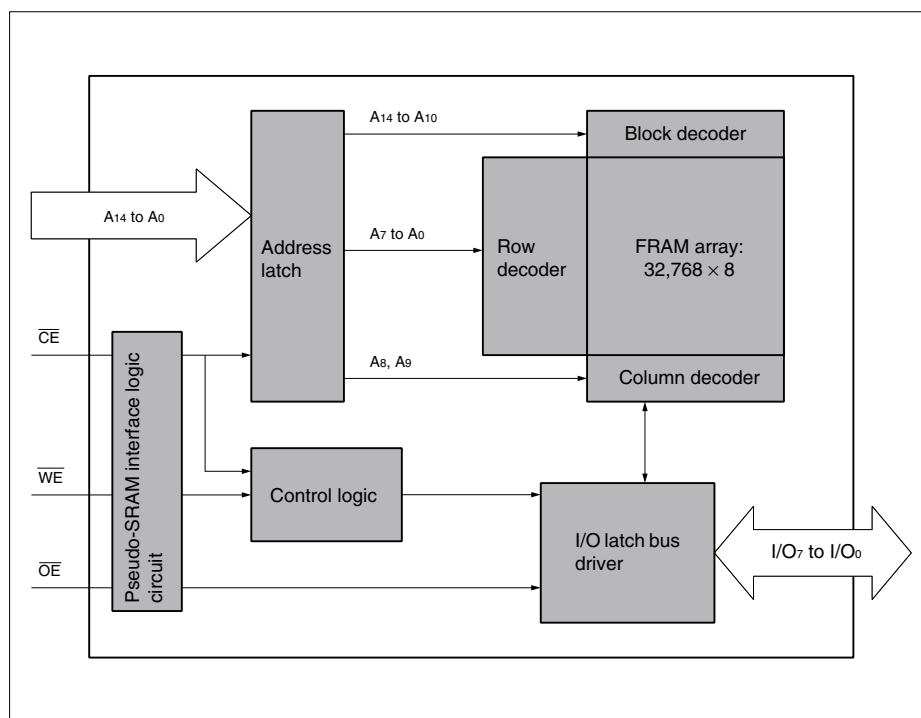
FPT-28P-M17



FPT-28P-M19

Pin No.	Pin name	Description
1 to 10, 21, 23 to 26	A ₀ to A ₁₄	Address input
11 to 13, 15 to 19	I/O ₀ to I/O ₇	Data input/output
20	$\overline{CE}$	Chip enable input
27	$\overline{WE}$	Write enable input
22	$\overline{OE}$	Output enable input
28	V _{CC}	Power supply (+3.3V Typ.)
14	GND	Ground

BLOCK DIAGRAM



NP501-00004-0v01-E